imall

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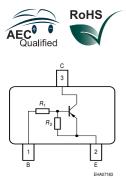
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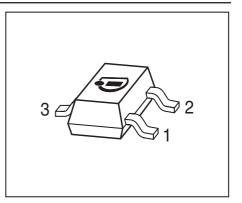




PNP Silicon Digital Transistor

- Built in bias resistor (R_1 = 2.2 k Ω , R_2 = 2.2 k Ω)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101





Туре	Marking	Pin Configuration			Package
BCR553	XBs	1=B	2=E	3=C	SOT23

Maximum Ratings

Junction - soldering point¹⁾

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	50	V	
Collector-base voltage	V _{CBO}	50		
Input forward voltage	V _{i(fwd)}	20		
Input reverse voltage	V _{i(rev)}	10		
Collector current	I _C	500	mA	
Total power dissipation-	P _{tot}	330	mW	
<i>T</i> _S ≤ 79 °C				
Junction temperature	T _i	150	°C	
Storage temperature	T _{stg}	-65 150		
Thermal Resistance				
Parameter	Symbol	Value	Unit	

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

K/W

≤ 215

R_{thJS}



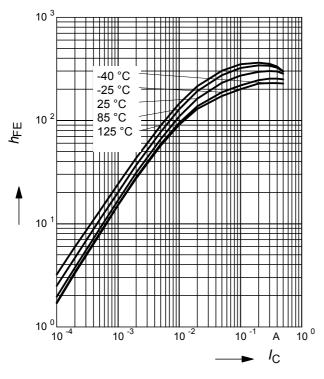
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics			i	Ĩ	
Collector-emitter breakdown voltage	V _{(BR)CEO}	50	-	-	V
<i>I</i> _C = 100 μA, <i>I</i> _B = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	50	-	-	
$I_{\rm C}$ = 10 µA, $I_{\rm E}$ = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB} = 50 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	3.5	mA
V _{EB} = 10 V, <i>I</i> _C = 0					
DC current gain-	h _{FE}	40	-	-	-
$I_{\rm C}$ = 50 mA, $V_{\rm CE}$ = 5 V					
Collector-emitter saturation voltage ¹⁾	V _{CEsat}	-	-	0.3	V
<i>I</i> _C = 50 mA, <i>I</i> _B = 2.5 mA					
Input off voltage	V _{i(off)}	0.6	-	1.5]
<i>I</i> _C = 100 μA, <i>V</i> _{CE} = 5 V					
Input on voltage	V _{i(on)}	1	-	1.8]
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 0.3 V					
Input resistor	R ₁	1.5	2.2	2.9	kΩ
Resistor ratio	R ₁ /R ₂	0.9	1	1.1	-
AC Characteristics					
Transition frequency	f _T	-	150	-	MHz
<i>I</i> _C = 50 mA, <i>V</i> _{CE} = 5 V, <i>f</i> = 100 MHz					
			•	•	•

Electrical Characteristics at $T_{\Delta} = 25^{\circ}$ C, unless otherwise specified

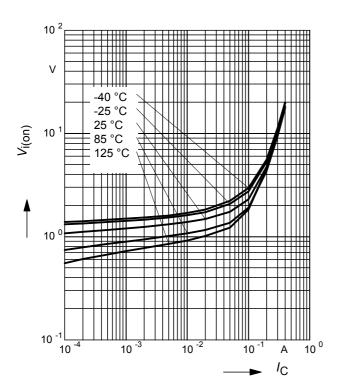
¹Pulse test: t < 300 μ s; D < 2%



DC current gain $h_{\text{FE}} = f(l_{\text{C}})$ $V_{\text{CE}} = 5 \text{ V}$ (common emitter configuration)

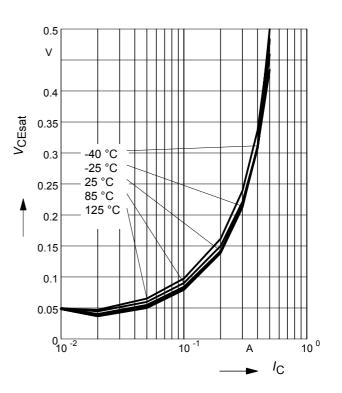


Input on Voltage $V_{i(on)} = f(I_C)$ $V_{CE} = 0.3V$ (common emitter configuration)

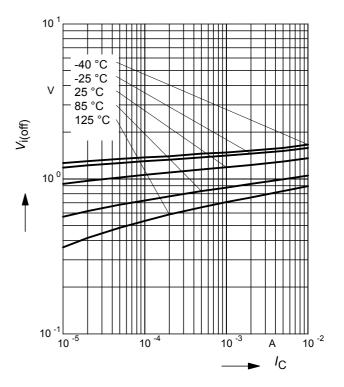


Collector-emitter saturation voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), I_{\text{C}}/I_{\text{B}} = 20$



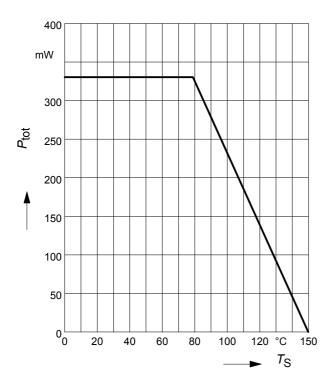
Input off voltage $V_{i(off)} = f(I_C)$ $V_{CE} = 5V$ (common emitter configuration)





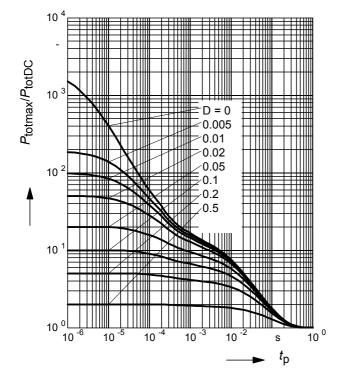
Total power dissipation $P_{tot} = f(T_S)$

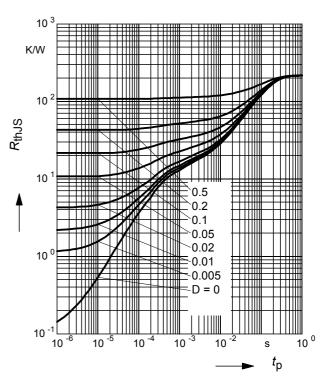
Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



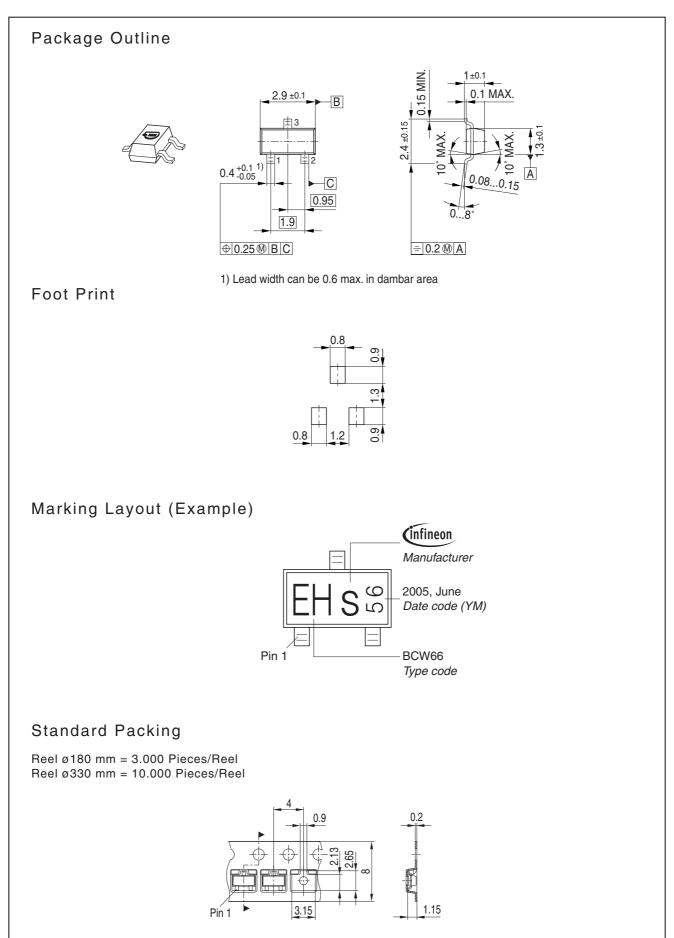
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$











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